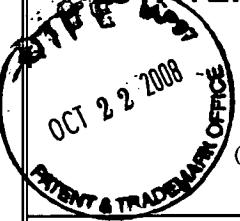


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				APPLICANT Makoto KITABATAKE, et al.		
				FILING DATE May 27, 2005	GROUP 2814	
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